



TSMC-99-132CC

October 15, 2003

To: Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/623,910 07/18/03

S.L. Shue, M.H. Tsai

METHOD FOR INTEGRATING LOW-K
MATERIALS IN SEMICONDUCTOR
FABRICATION

Grp. Art Unit: _____

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.


The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56. Copies of each document is included herewith.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on October 20, 2003.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 10/20/03

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U.S. Patent 5,827,776 to Bandyopadhyay et al., "Method of Making an Integrated Circuit which Uses an Etch Stop for Producing Staggered Interconnect Lines", discloses a multilevel interconnect structure using staggered interconnects to reduce electric field coupling between interconnect lines.

U.S. Patent 5,602,423 to Jain, "Damascene Conductors with Embedded Pillars", discloses damascene conductors with embedded pillars to prevent erosion during chemical-mechanical polishing.

U.S. Patent 5,110,712 to Kessler et al., "Incorporation of Dielectric Layers in a Semiconductor", discloses a metal interconnect in a polymer, low-K dielectric layer.

U.S. Patent 5,744,394 to Iguchi et al., "Method for Fabricating a Semiconductor Device Having Copper Layer", discloses a dual damascene process for forming interconnections.

Sincerely,

A handwritten signature in black ink, appearing to be 'SBA', with a long horizontal line extending to the right.

Stephen B. Ackerman,
Reg. No. 37761

